

NTTFS4821N

MOSFET – Power, Single, N-Channel, μ 8FL 30 V, 57 A

Features

- Small Footprint (3.3 x 3.3 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- DC-DC Converters
- High Side Switching

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

| Parameter | Symbol | Value | Unit | |
|--|--|--------------------------|------------------|---|
| Drain-to-Source Voltage | V_{DS} | 30 | V | |
| Gate-to-Source Voltage | V_{GS} | ± 20 | V | |
| Continuous Drain Current $R_{\theta JA}$ (Note 1) | I_D | $T_A = 25^\circ\text{C}$ | 13.5 | A |
| | | $T_A = 85^\circ\text{C}$ | 9.7 | |
| Power Dissipation $R_{\theta JA}$ (Note 1) | P_D | $T_A = 25^\circ\text{C}$ | 2.1 | W |
| | | $T_A = 85^\circ\text{C}$ | | |
| Continuous Drain Current $R_{\theta JA} \leq 10$ s (Note 1) | I_D | $T_A = 25^\circ\text{C}$ | 18.6 | A |
| | | $T_A = 85^\circ\text{C}$ | 13.4 | |
| Power Dissipation $R_{\theta JA} \leq 10$ s (Note 1) | P_D | $T_A = 25^\circ\text{C}$ | 4.1 | W |
| | | $T_C = 25^\circ\text{C}$ | | |
| Continuous Drain Current $R_{\theta JA}$ (Note 2) | I_D | $T_C = 25^\circ\text{C}$ | 7.5 | A |
| | | $T_C = 85^\circ\text{C}$ | 5.4 | |
| Power Dissipation $R_{\theta JA}$ (Note 2) | P_D | $T_C = 25^\circ\text{C}$ | 0.66 | W |
| | | $T_C = 25^\circ\text{C}$ | | |
| Continuous Drain Current $R_{\theta JC}$ (Note 1) | I_D | $T_C = 25^\circ\text{C}$ | 57 | A |
| | | $T_C = 85^\circ\text{C}$ | 41 | |
| Power Dissipation $R_{\theta JC}$ (Note 1) | P_D | $T_C = 25^\circ\text{C}$ | 38.5 | W |
| | | $T_C = 25^\circ\text{C}$ | | |
| Pulsed Drain Current | $T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ | I_{DM} | 171 | A |
| Operating Junction and Storage Temperature | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ | |
| Source Current (Body Diode) | I_S | 38.5 | A | |
| Drain to Source dV/dt | dV/dt | 6.0 | V/ns | |
| Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}, V_{DD} = 50$ V, $V_{GS} = 10$ V, $I_L = 33$ A _{pk} , $L = 0.1$ mH, $R_G = 25 \Omega$) | E_{AS} | 55 | mJ | |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | T_L | 260 | $^\circ\text{C}$ | |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.

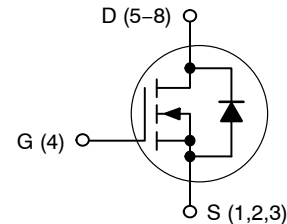


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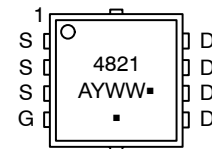
<http://onsemi.com>

| $V_{(BR)DSS}$ | $R_{DS(on)}$ MAX | I_D MAX |
|---------------|-------------------------|-----------|
| 30 V | 7.0 m Ω @ 10 V | 57 A |
| | 10.8 m Ω @ 4.5 V | |

N-Channel MOSFET



MARKING DIAGRAM



4821 = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping† |
|---------------|-----------------|------------------|
| NTTFS4821NTAG | WDFN8 (Pb-Free) | 1500/Tape & Reel |
| NTTFS4821NTWG | WDFN8 (Pb-Free) | 5000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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2. Surface-mounted on FR4 board using the minimum recommended pad size.

THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter | Symbol | Value | Unit |
|---|-----------------|-------|------|
| Junction-to-Case (Drain) | $R_{\theta JC}$ | 3.25 | °C/W |
| Junction-to-Ambient – Steady State (Note 3) | $R_{\theta JA}$ | 58.3 | |
| Junction-to-Ambient – Steady State (Note 4) | $R_{\theta JA}$ | 188.4 | |
| Junction-to-Ambient – ($t \leq 10$ s) (Note 3) | $R_{\theta JA}$ | 30.6 | |

3. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | | |
|---|-------------------|-------------------------------------|---------------------------|----|--|-----------|---------|
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0$ V, $I_D = 250$ μ A | 30 | | | V | |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | | | 25 | | mV/°C | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS} = 0$ V, $V_{DS} = 24$ V | $T_J = 25^\circ\text{C}$ | | | 1.0 | μ A |
| | | | $T_J = 125^\circ\text{C}$ | | | 10 | |
| Gate-to-Source Leakage Current | I_{GSS} | $V_{DS} = 0$ V, $V_{GS} = \pm 20$ V | | | | ± 100 | nA |

ON CHARACTERISTICS (Note 5)

| | | | | | | | |
|--|------------------|---|--------------|-----|-----|-------|------------|
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}$, $I_D = 250$ μ A | 1.5 | 1.9 | 2.5 | V | |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | 6 | | mV/°C | |
| Drain-to-Source On Resistance | $R_{DS(on)}$ | $V_{GS} = 10$ V to 11.5 V | $I_D = 20$ A | | 5.8 | 7.0 | m Ω |
| | | | $I_D = 10$ A | | 5.7 | | |
| | | $V_{GS} = 4.5$ V | $I_D = 20$ A | | 8.8 | 10.8 | |
| | | | $I_D = 10$ A | | 8.6 | | |
| Forward Transconductance | g_{FS} | $V_{DS} = 15$ V, $I_D = 30$ A | | 53 | | S | |

CHARGES AND CAPACITANCES

| | | | | | | |
|------------------------------|--------------|---|--|------|------|----|
| Input Capacitance | C_{iss} | $V_{GS} = 0$ V, $f = 1.0$ MHz, $V_{DS} = 12$ V | | 1300 | 1755 | pF |
| Output Capacitance | C_{oss} | | | 300 | 405 | |
| Reverse Transfer Capacitance | C_{rss} | | | 150 | 233 | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = 4.5$ V, $V_{DS} = 15$ V, $I_D = 30$ A | | 10.5 | 15 | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | 1.3 | | |
| Gate-to-Source Charge | Q_{GS} | | | 3.9 | | |
| Gate-to-Drain Charge | Q_{GD} | | | 4.5 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | | $V_{GS} = 11.5$ V, $V_{DS} = 15$ V, $I_D = 20$ A | | 24 | |

SWITCHING CHARACTERISTICS (Note 6)

| | | | | | | |
|---------------------|--------------|--|--|-----|--|----|
| Turn-On Delay Time | $t_{d(on)}$ | $V_{GS} = 4.5$ V, $V_{DS} = 15$ V, $I_D = 15$ A, $R_G = 3.0$ Ω | | 12 | | ns |
| Rise Time | t_r | | | 22 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 16 | | |
| Fall Time | t_f | | | 4.5 | | |

5. Pulse Test: pulse width = 300 μ s, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

SWITCHING CHARACTERISTICS (Note 6)

| | | | | | | |
|---------------------|--------------|---|--|-----|--|----|
| Turn-On Delay Time | $t_{d(on)}$ | $V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 15\text{ A}, R_G = 3.0\ \Omega$ | | 8.5 | | ns |
| Rise Time | t_r | | | 20 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 23 | | |
| Fall Time | t_f | | | 2.8 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|-------------------------|----------|--|---------------------------|--|------|-----|----|
| Forward Diode Voltage | V_{SD} | $V_{GS} = 0\text{ V},$ $I_S = 20\text{ A}$ | $T_J = 25^\circ\text{C}$ | | 0.9 | 1.0 | V |
| | | | $T_J = 125^\circ\text{C}$ | | 0.78 | | |
| Reverse Recovery Time | t_{RR} | $V_{GS} = 0\text{ V},$ $dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 20\text{ A}$ | | | 9.0 | | ns |
| Charge Time | t_a | | | | 6.5 | | |
| Discharge Time | t_b | | | | 2.5 | | |
| Reverse Recovery Charge | Q_{RR} | | | | 1.7 | | |

PACKAGE PARASITIC VALUES

| | | | | | | |
|-------------------|-------|--------------------------|--|-------|-----|----|
| Source Inductance | L_S | $T_A = 25^\circ\text{C}$ | | 0.38 | | nH |
| Drain Inductance | L_D | | | 0.054 | | |
| Gate Inductance | L_G | | | 1.3 | | |
| Gate Resistance | R_G | | | 0.6 | 2.0 | |

5. Pulse Test: pulse width = 300 μs , duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

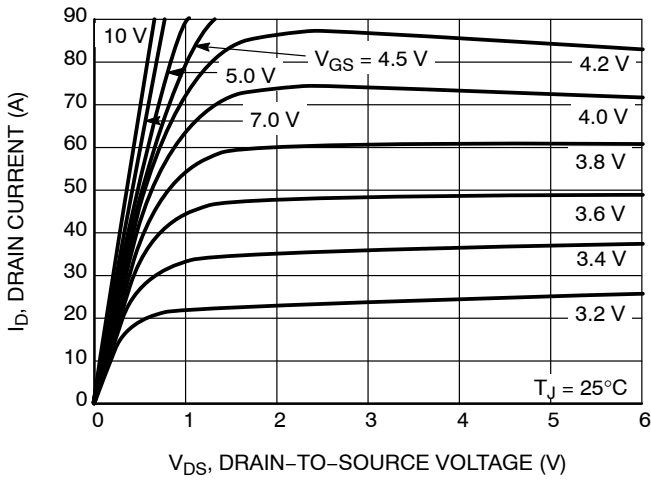


Figure 1. On-Region Characteristics

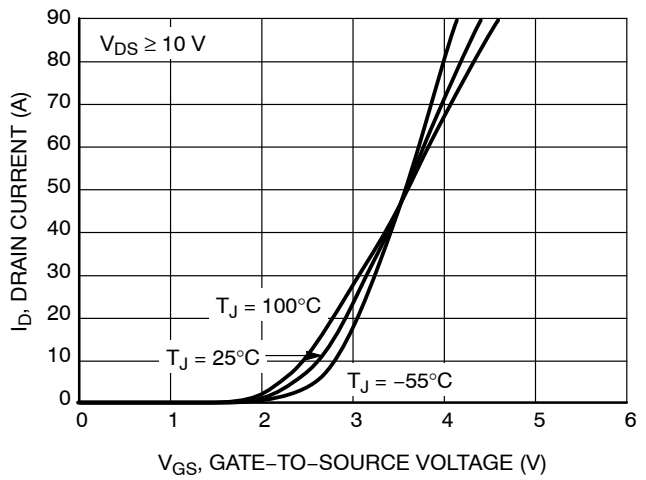


Figure 2. Transfer Characteristics

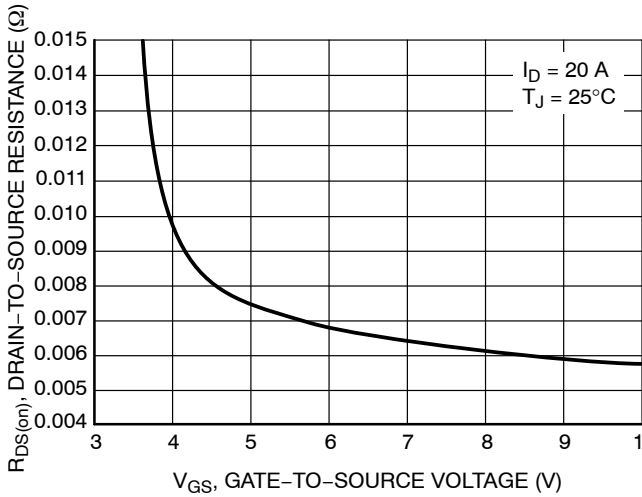


Figure 3. On-Resistance vs. Gate-to-Source Voltage

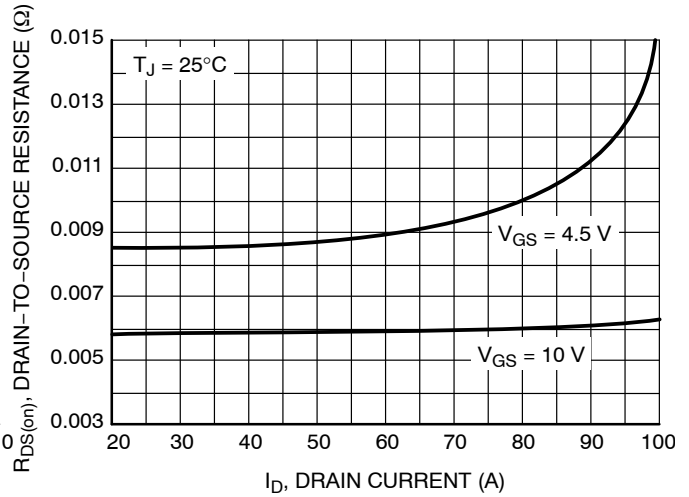


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

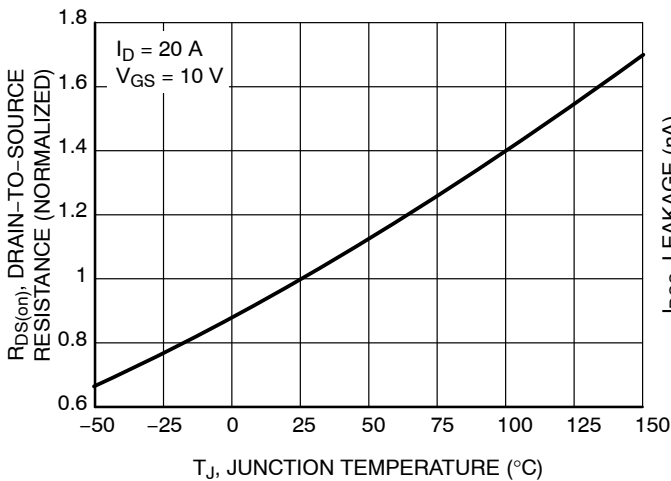


Figure 5. On-Resistance Variation with Temperature

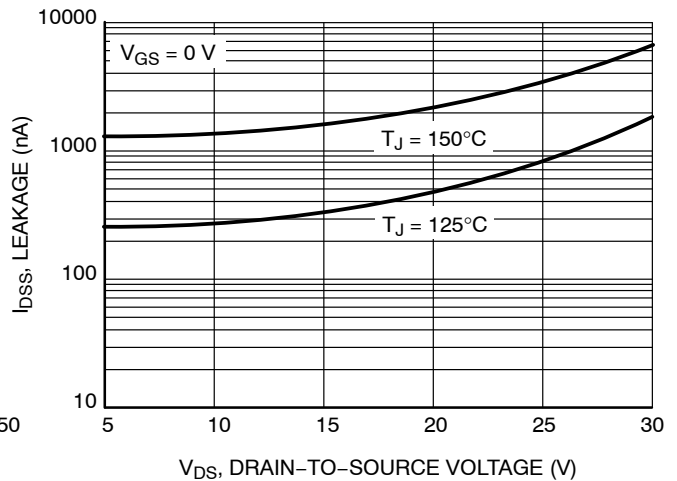


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

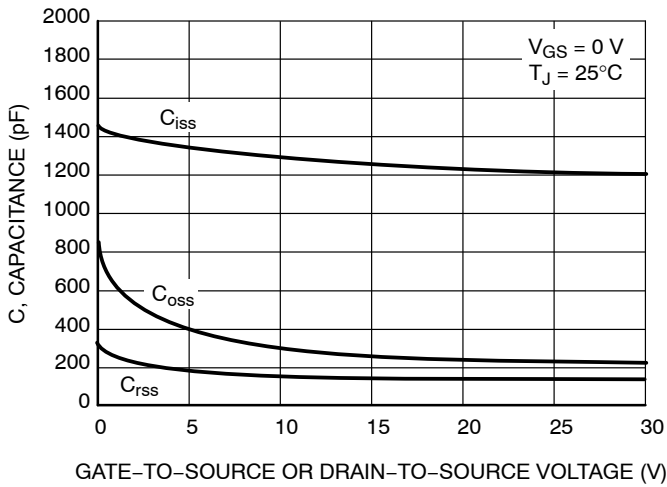


Figure 7. Capacitance Variation

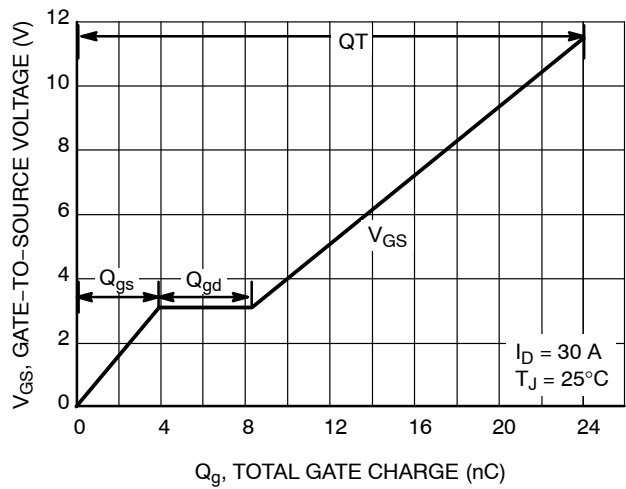


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

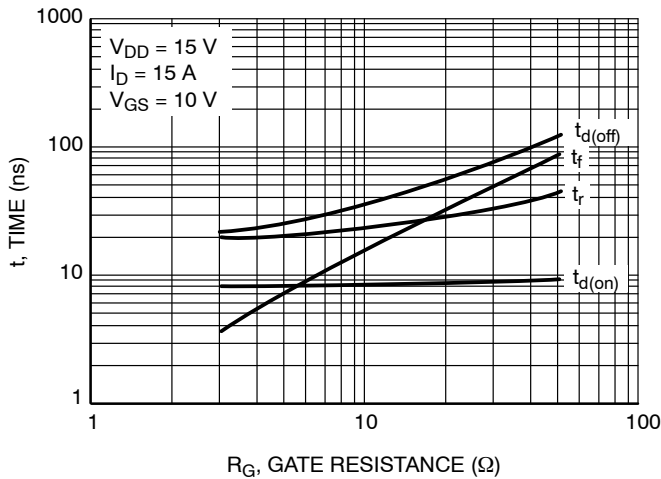


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

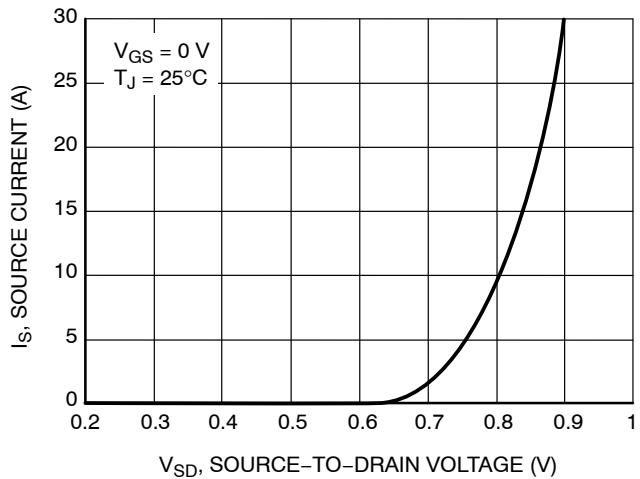


Figure 10. Diode Forward Voltage vs. Current

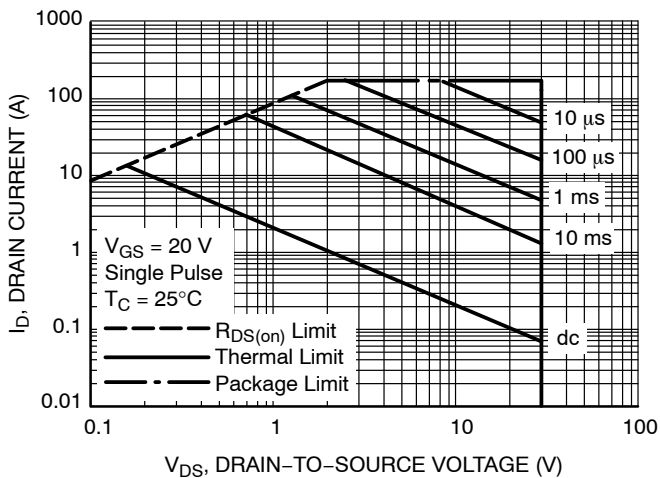


Figure 11. Maximum Rated Forward Biased Safe Operating Area

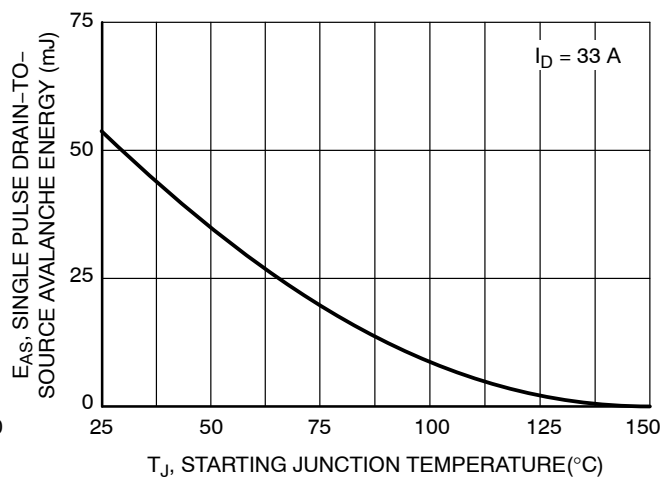


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 2:1

WDFN8 3.3x3.3, 0.65P CASE 511AB ISSUE D

DATE 23 APR 2012



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|-----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.70 | 0.75 | 0.80 | 0.028 | 0.030 | 0.031 |
| A1 | 0.00 | --- | 0.05 | 0.000 | --- | 0.002 |
| b | 0.23 | 0.30 | 0.40 | 0.009 | 0.012 | 0.016 |
| c | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| D | 3.30 BSC | | | 0.130 BSC | | |
| D1 | 2.95 | 3.05 | 3.15 | 0.116 | 0.120 | 0.124 |
| D2 | 1.98 | 2.11 | 2.24 | 0.078 | 0.083 | 0.088 |
| E | 3.30 BSC | | | 0.130 BSC | | |
| E1 | 2.95 | 3.05 | 3.15 | 0.116 | 0.120 | 0.124 |
| E2 | 1.47 | 1.60 | 1.73 | 0.058 | 0.063 | 0.068 |
| E3 | 0.23 | 0.30 | 0.40 | 0.009 | 0.012 | 0.016 |
| e | 0.65 BSC | | | 0.026 BSC | | |
| G | 0.30 | 0.41 | 0.51 | 0.012 | 0.016 | 0.020 |
| K | 0.65 | 0.80 | 0.95 | 0.026 | 0.032 | 0.037 |
| L | 0.30 | 0.43 | 0.56 | 0.012 | 0.017 | 0.022 |
| L1 | 0.06 | 0.13 | 0.20 | 0.002 | 0.005 | 0.008 |
| M | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 |
| θ | 0° | --- | 12° | 0° | --- | 12° |

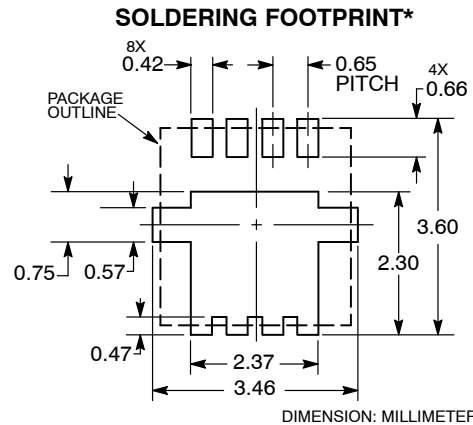


GENERIC MARKING DIAGRAM*



- XXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "▪", may or may not be present.



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| | | |
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| DESCRIPTION: | WDFN8 3.3X3.3, 0.65P | PAGE 1 OF 1 |

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